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Contents

vii Authors
ix Conference Committee

EUV READINESS: JOINT SESSION WITH CONFERENCES 10450 AND 10451

10450 05 EUV mask manufacturing readiness in the merchant mask industry [10450-4]

EUV MASK INSPECTION: JOINT SESSION WITH CONFERENCES 10451 AND 10450

10450 06 Classification and printability of EUV mask defects from SEM images [10450-5]
10450 07 Actinic inspection of EUV reticles with arbitrary pattern design [10450-6]

EUV MASK METROLOGY AND INSPECTION: JOINT SESSION WITH CONFERENCES 10450 AND 10451

10450 08 Measurement of through-focus EUV pattern shifts using the SHARP actinic microscope [10450-7]

EUV MASK PELLICLE: JOINT SESSION WITH CONFERENCES 10451 AND 10450

10450 0B Efficient simulation of EUV pellicles [10450-11]

EUV MASK AND IMAGING

10450 0C EUV source optimization driven by fundamental diffraction considerations [10450-12]
10450 0F Individual multilayer reflectance and near field image formation in an EUV reticle [10450-16]

EUV RESIST I

10450 0H Unraveling the role of secondary electrons upon their interaction with photoresist during EUV exposure [10450-17]

EUV RESISTS II

10450 0P Reducing roughness in extreme ultraviolet lithography [10450-25]
HIGH-NA EUV LITHOGRAPHY

10450 0V  Optical proximity correction for anamorphic extreme ultraviolet lithography [10450-31]

EUV SOURCE

10450 0Z  High-power LPP-EUV source with long collector mirror lifetime for high volume semiconductor manufacturing [10450-35]

EUV PATTERNING AND PROCESS ENHANCEMENT I

10450 17  EUV local CDU healing performance and modeling capability towards 5nm node [10450-43]
10450 18  Roadmap evolution: from NTRS to ITRS, from ITRS 2.0 to IRDS [10450-44]

EUV PATTERNING AND PROCESS ENHANCEMENT II

10450 1A  Development of amorphous silicon based EUV hardmasks through physical vapor deposition [10450-46]

POSTER SESSION: EUV SOURCE

10450 1C  Key components development progress updates of the 250W high power LPP-EUV light source [10450-48]

POSTER SESSION: EUV RESISTS AND PROCESS

10450 1E  A study on enhancing EUV resist sensitivity (2) [10450-50]
10450 1F  Technology for defectivity improvement in resist coating and developing process in EUV lithography process [10450-51]
10450 1H  Development of the negative-tone molecular resists for EB/EUVL having high EUV absorption capacity and molecular design method [10450-53]

POSTER SESSION: EUV PELLICLES

10450 1K  Lifetime estimation of extreme-ultraviolet pellicle at 500 W source power by thermal stress analysis [10450-56]
10450 1L  Characterization of pellicle membranes by lab-based spectroscopic reflectance and transmittance measurements in the extreme ultraviolet [10450-57]
<table>
<thead>
<tr>
<th>Session</th>
<th>Title</th>
</tr>
</thead>
<tbody>
<tr>
<td>1M</td>
<td>Search for multi-stack EUV pellicle membrane for EUV non-actinic mask inspection [10450-58]</td>
</tr>
<tr>
<td>1N</td>
<td>Thermo-mechanical behavior analysis of extreme-ultraviolet pellicle cooling with H2 flow [10450-59]</td>
</tr>
<tr>
<td>1O</td>
<td>Lifetime impact on residual stress of EUV pellicle [10450-60]</td>
</tr>
<tr>
<td>1Q</td>
<td>Wrinkle formation analysis in extreme-ultraviolet pellicle [10450-62]</td>
</tr>
</tbody>
</table>

**POSTER SESSION: EUV PATTERNING AND PROCESS ENHANCEMENT**

| 1T     | Contrast matching of line gratings obtained with NXE3XXX and EUV-interference lithography [10450-65] |
| 1U     | Coater/developer based techniques to improve high-resolution EUV patterning defectivity [10450-66] |

**POSTER SESSION: EUV MASK METROLOGY, INSPECTION, AND IMAGING**

| 1X     | Applications of RCWA on EUV mask optics [10450-70] |

**POSTER SESSION: EUV HARDWARE**

| 21     | Extreme ultra violet lithographic optical projection system design method using Code V lens module and generalized Gaussian constants [10450-72] |
| 24     | A new objective for EUV lithography, EUV microscopy, and 2D x-ray imaging [10450-75] |
| 27     | Characterization of EBL2 EUV exposure facility [10450-78] |
| 2A     | Optimized phase-shifting masks for high-resolution resist patterning by interference lithography [10450-81] |
Authors

Numbers in the index correspond to the last two digits of the seven-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first five digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Abe, Tamotsu, 0Z, 1C
Adam, Kostas, 0V
Bahrenberg, Lukas, 1L, 2A
Ban, Chung-Hyun, 1K
Berk, Markus, 08
Bitter, Manfred L., 24
Broman, Par, 0C
Brose, Sascha, 1L, 2A
Cao, Yong, 1A
Chen, Alek, 05
Chen, Yulu, 08
Chiou, Tsann-Bim, 05
Cho, Wonil, 17
Choi, Peter, 17
Choi, Yohan, 05
Clifford, Chris, 0V
Custers, Rolf, 1T
Dai, Huixiong, 1A
Danylyuk, Serhiy, 1L, 2A
De Silva, Anuja, 1A, 1U
de Simone, Danilo, 0H
Delgado-Aparicio, Luis F., 24
Deutz, Alex F., 27
DeVries, Scott, 1A
Diehl, Daniel L., 1A
Dong, Lisong, 1X
Echigo, Masatoshi, 1H
Effrinion, Philip C., 24
Ekinci, Yasin, 07, 1T
Enomoto, Masashi, 1F
Erdmann, A., 0B
Evanschitzky, P., 0B
Fallica, Roberto, 1T
Fan, Taian, 1X
Felix, Nelson M., 1A, 1U
Fenger, Germain, 0V
Fernandez, Sara, 07
Finders, Jo, 0C
Fonseca, Carlos, 17
Foubert, Philippe, 1F
Gallagher, Emily, 1L
Gao, Lan, 24
Gao, Weimin, 0F
Gargnini, Paolo A., 18
Goldberg, Kenneth, 08
Green, Michael, 05
Ham, Young, 05
Harada, Tetsuo, 1E, 1H
Hashimoto, Yusaku, 1U
Helfenstein, Patrick, 07
Hetzer, Dave, 1U
Hill, Kenneth W., 24
Hoefnagels, Rik, 1T
Hontake, Koichii, 1U
Hori, Tsukasa, 0Z, 1C
Hsiao, Li-Jen, 21
Hubbard, Alex, 1U
Hull, Lior, 1U
Hur, Su-Mi, 1M
Ichinomiya, Hiroshi, 1F
Ishii, Takuya, 1C
Isayan, Artak, 0F
Itou, Noritoshi, 1C
Jee, Tae Kwon, 17
Jeong, Hae-Nam, 1Q
Jiang, Fan, 0V
Jiang, Jing, 0H
Johnson, Richard, 1U
Juschkine, Larissa, 2A
Kamberian, Henry, 05, 08
Kamei, Yuya, 1F
Kandel, Yudhi, 0F
Kang, Myung-Gi, 1N
Kasprowicz, Bryan, 08
Kawakami, Shinichiro, 1F, 1U
Kawasuiji, Yasufumi, 0Z, 1C
Kazazis, Dimitrios, 07
Kerkhof, Peter J., 27
Kim, Guk-Jin, 1M, 1Q
Kim, Min-Woo, 1O
Ko, Akiteru, 1U
Kodama, Takeshi, 0Z, 1C
Koike, Kyochii, 17
Koster, Norbert B., 27
Kraus, Brian F., 24
Kudo, Hiroto, 1H
Lam, Michael, 0V
Lammers, Ad, 05
Lebert, Rainer, 2A
Lee, Sung-Gyu, 1M, 1N, 1O, 1Q
Lemley, Corey, 1U
Lin, Hoang-Yan, 21
Liu, Eric, 1U
Loosen, Peter, 1L, 2A
Lu, Jian, 24
Mack, Chris A., 0P
Mangat, Pawitter, 0B
Matsumoto, Yoko, 1E
McCord, Jeremy, 08
McNamara, John, 0C
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